

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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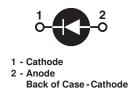
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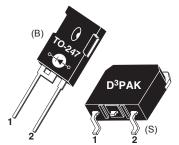
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APT15D120B(G) 1200V 15A APT15D120S(G) 1200V 15A

*G Denotes RoHS Compliant, Pb Free Terminal Finish.

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

PRODUCT APPLICATIONS	PRODUCT FEATURES	PRODUCT BENEFITS
 Anti-Parallel Diode -Switchmode Power Supply 	 Ultrafast Recovery Times 	• Low Losses
-Inverters	 Soft Recovery Characteristics 	 Low Noise Switching
 Free Wheeling Diode Motor Controllers 	 Popular TO-247 Package or Surface Mount D³PAK Package 	 Cooler Operation
-Converters • Snubber Diode	Low Forward Voltage	 Higher Reliability Systems
Uninterruptible Power Supply (UPS)Induction Heating	High Blocking Voltage	 Increased System Power Density
High Speed Rectifiers	Low Leakage Current	Delisity

MAXIMUM RATINGS All Ratings: $T_C = 25^{\circ}C$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT15D120B_S(G)	UNIT
V_R	Maximum D.C. Reverse Voltage		
V _{RRM}	Maximum Peak Repetitive Reverse Voltage	1200	Volts
V _{RWM}	Maximum Working Peak Reverse Voltage		
I _F (AV)	Maximum Average Forward Current (T _C = 98°C, Duty Cycle = 0.5)	15	
I _F (RMS)	RMS Forward Current (Square wave, 50% duty)	24	Amps
I _{FSM}	Non-Repetitive Forward Surge Current (T _J = 45°C, 8.3ms)	110	
T_J , T_{STG}	Operating and StorageTemperature Range	-55 to 150	°C
T _L	Lead Temperature for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

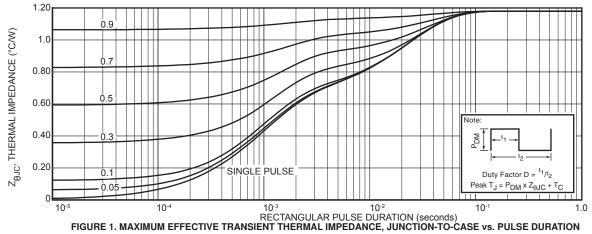
Symbol			MIN	TYP	MAX	UNIT
V _F		I _F = 15A		2.0	2.5	Volts
		I _F = 30A		2.3		
		I _F = 15A, T _J = 125°C		1.8		
I _{RM}	Maximum Reverse Leakage Current	$V_R = V_R$ Rated			250	- μΑ
		$V_R = V_R$ Rated, $T_J = 125$ °C			500	
C _T	Junction Capacitance, V _R = 200V	•		17		pF

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t _{rr}	Reverse Recovery Time $I_F = 1A$, $di_F/dt = -100A/\mu s$, $V_R = 30V$, $T_J = 25^{\circ}C$		-	32		ns
t _{rr}	Reverse Recovery Time		ı	260		113
Q_{rr}	Reverse Recovery Charge	$I_F = 15A, di_F/dt = -200A/\mu s$ $V_R = 800V, T_C = 25^{\circ}C$	-	480		nC
I _{RRM}	Maximum Reverse Recovery Current	R - 000 V, 1 C - 23 C	1	4	-	Amps
t _{rr}	Reverse Recovery Time	$I_F = 15A$, $di_F/dt = -200A/\mu s$ $V_R = 800V$, $T_C = 125^{\circ}C$	-	370		ns
Q _{rr}	Reverse Recovery Charge		-	1300		nC
I _{RRM}	Maximum Reverse Recovery Current		-	9	-	Amps
t _{rr}	Reverse Recovery Time	$I_F = 15A$, $di_F/dt = -1000A/\mu s$ $V_R = 800V$, $T_C = 125$ °C	-	140		ns
Q _{rr}	Reverse Recovery Charge		-	2000		nC
I _{RRM}	Maximum Reverse Recovery Current		_	28		Amps

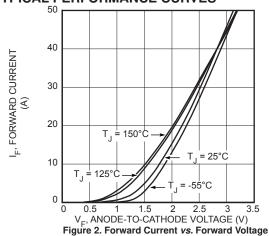
THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.18	°C/W
R _{0JA}	Junction-to-Ambient Thermal Resistance			40	
W _T	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.



TYPICAL PERFORMANCE CURVES



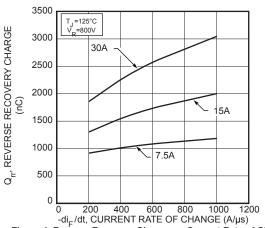
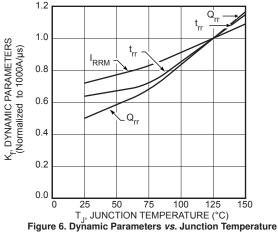


Figure 4. Reverse Recovery Charge vs. Current Rate of Change



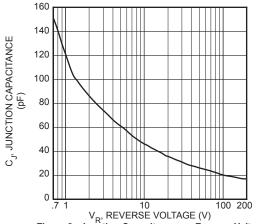


Figure 8. Junction Capacitance vs. Reverse Voltage

APT15D120B_S(G)

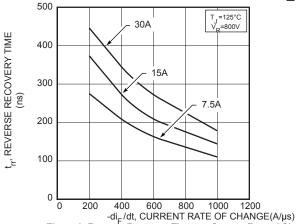


Figure 3. Reverse Recovery Time vs. Current Rate of Change

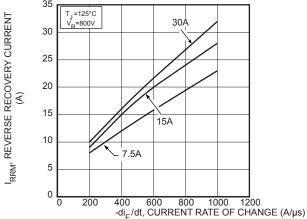


Figure 5. Reverse Recovery Current vs. Current Rate of Change

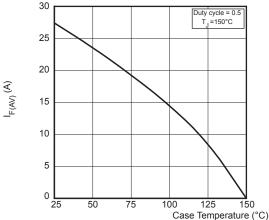


Figure 7. Maximum Average Forward Current vs. CaseTemperature

Figure 9. Diode Test Circuit

- 1 I_F Forward Conduction Current
 2 di_F/dt Rate of Diode Current Change Through Zero Crossing.
 3 I_{RRM} Maximum Reverse Recovery Current.
 4 t_{rr} Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and 0.25 •I_{RRM} passes through zero.
- $\mathbf{5}$ Q_{rr} Area Under the Curve Defined by I_{RRM} and t_{rr} .

Figure 10, Diode Reverse Recovery Waveform and Definitions

